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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**Applicants** 

Ritzdorf et al.

Application No.

09/018,783

Confirmation No.: 1242

Filed

2/4/98

For

METHOD AND APPARATUS FOR LOW TEMPERATURE

ANNEALING OF METALLIZATION MICRO-STRUCTURES

IN THE PRODUCTION OF A MICROELECTRONIC DEVICE

Examiner

: Deven M. Collins

Art Unit

: 2823

Docket No.

: 29195.8162US

Date

: October 1, 2001

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Commissioner for Patents Washington, DC 20231

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In accordance with 37 C.F.R. §§ 1.56 and 1.97 through 1.98, applicants wish to make known to the Patent and Trademark Office the references set forth on the attached form PTO/SB/08A (copies of the cited references, as required under 37 C.F.R. § 1.98, are enclosed). Although the aforesaid references are made known to the Patent and Trademark Office in compliance with applicants' duty to disclose all information of which they are aware that is believed relevant to the patentability of the above-identified application, applicants believe that their invention is patentable. As to any document supplied, applicants do not admit that it is "prior art" under 35 U.S.C. §§ 102 or 103, and

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Please acknowledge receipt of this Information Disclosure Statement and kindly make the cited references of record in the above-identified application. As the present information disclosure statement is being filed as a submission under 37 CFR §1.114(a), no fee is believed necessary under 37 CFR §1.97. If any such fee is necessitated by this filing, such fees may be charged to Deposit Account 50-0665.

Respectfully submitted,

Perkins Coje LLP

Edward S. Hotchkiss Registration No. 33,904

ESH:scc

Enclosures:

Postcard Form PTO/SB/08A Cited References (39)

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